



IMPORTANT NOTICE

10 December 2015

1. Global joint venture starts operations as WeEn Semiconductors

Dear customer,

As from November 9th, 2015 NXP Semiconductors N.V. and Beijing JianGuang Asset Management Co. Ltd established Bipolar Power joint venture (JV), **WeEn Semiconductors**, which will be used in future Bipolar Power documents together with new contact details.

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Thank you for your cooperation and understanding,

WeEn Semiconductors



1. General description

Planar passivated very sensitive gate Silicon Controlled Rectifier in a SOT54 (TO-92) plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate

3. Applications

- Ignition circuits
- Low power latching circuits
- Protection / shut-down circuits: lighting ballasts
- Protection / shut-down circuits: Switched Mode Power Supplies

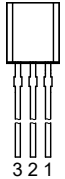

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	-	400	V
V_{RRM}	repetitive peak reverse voltage		-	-	400	V
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 8.3\text{ ms}$	-	-	9	A
		half sine wave; $T_{j(init)} = 25\text{ °C}$; $t_p = 10\text{ ms}$; Fig. 4 ; Fig. 5	-	-	8	A
T_j	junction temperature		-	-	125	°C
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$; Fig. 1	-	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 83\text{ °C}$; Fig. 2 ; Fig. 3	-	-	0.8	A
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ °C}$; Fig. 7	-	-	50	μA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$; $T_j = 125\text{ °C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	500	800	-	V/ μs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A	anode	 <p>TO-92 (SOT54)</p>	
2	G	gate		
3	K	cathode		

6. Ordering information

Table 3. Ordering information

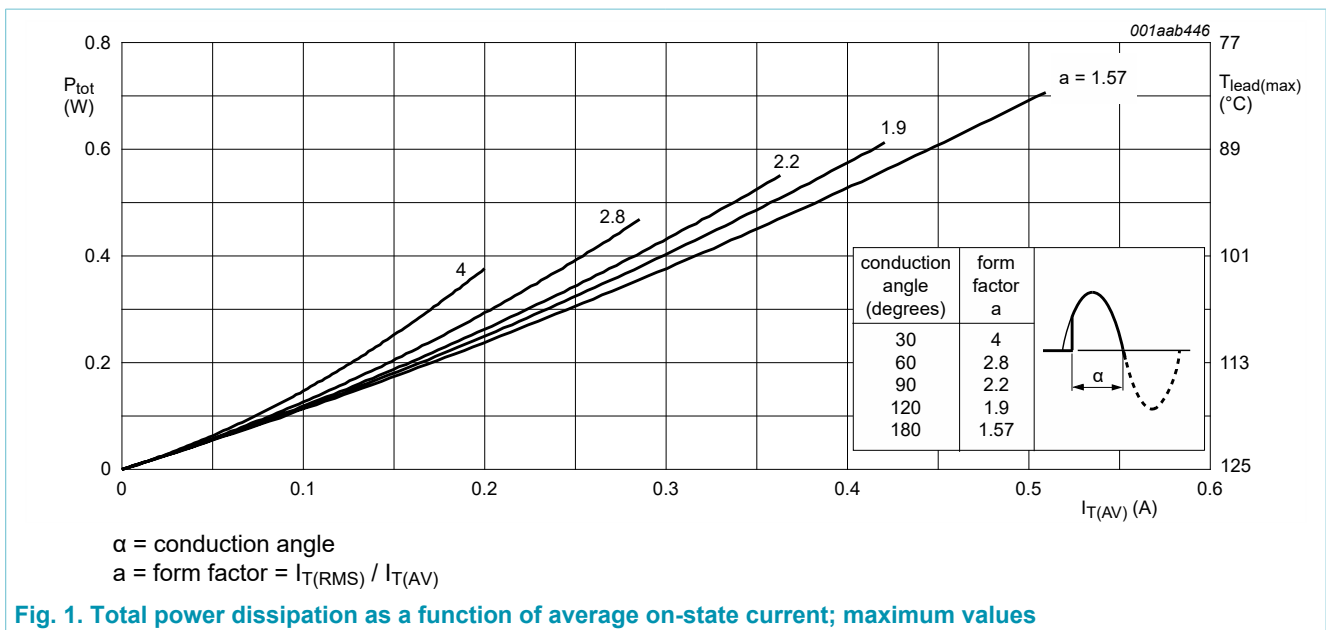
Type number	Package		
	Name	Description	Version
BT169D-L	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
V_{RRM}	repetitive peak reverse voltage		-	400	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$; Fig. 1	-	0.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{lead} \leq 83\text{ }^{\circ}\text{C}$; Fig. 2; Fig. 3	-	0.8	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 8.3\text{ ms}$	-	9	A
		half sine wave; $T_{j(init)} = 25\text{ }^{\circ}\text{C}$; $t_p = 10\text{ ms}$; Fig. 4; Fig. 5	-	8	A
I^2t	I^2t for fusing	$t_p = 10\text{ ms}$; SIN	-	0.32	A^2s
dl_T/dt	rate of rise of on-state current	$I_T = 2\text{ A}$; $I_G = 10\text{ mA}$; $dl_G/dt = 100\text{ mA}/\mu\text{s}$	-	50	$\text{A}/\mu\text{s}$
I_{GM}	peak gate current		-	1	A
V_{RGM}	peak reverse gate voltage		-	5	V
P_{GM}	peak gate power		-	2	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.1	W
T_{stg}	storage temperature		-40	150	$^{\circ}\text{C}$
T_j	junction temperature		-	125	$^{\circ}\text{C}$



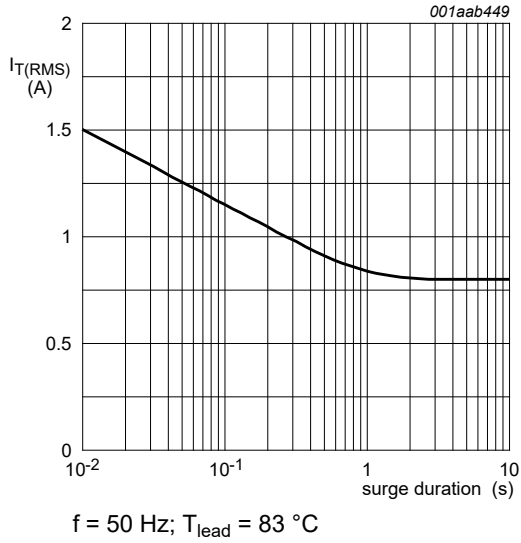


Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

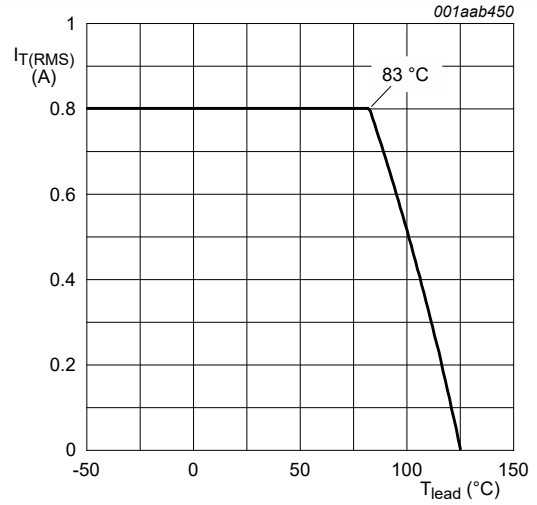


Fig. 3. RMS on-state current as a function of lead temperature; maximum values

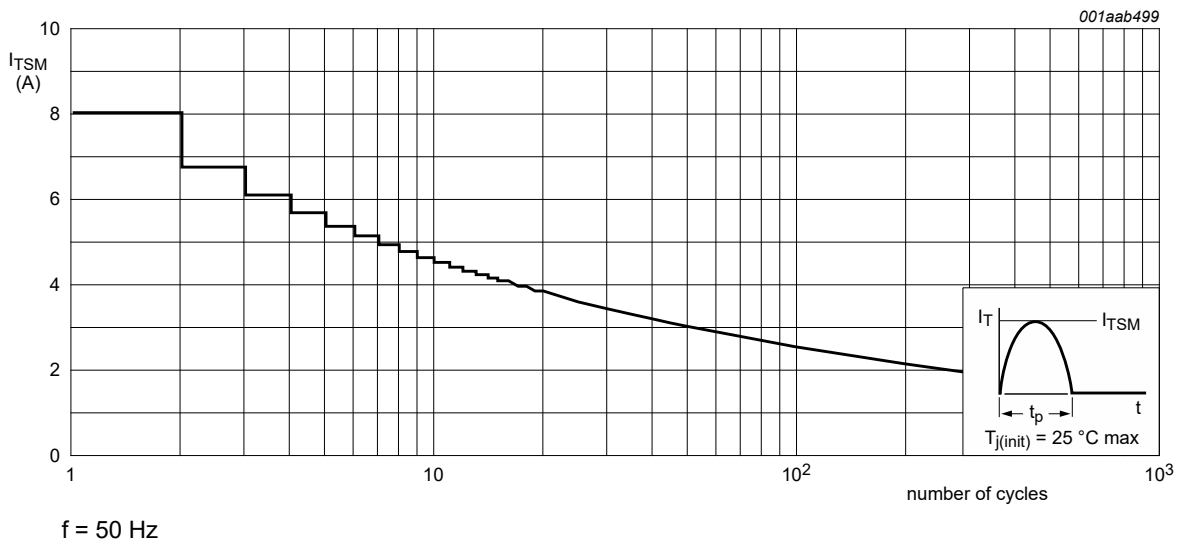
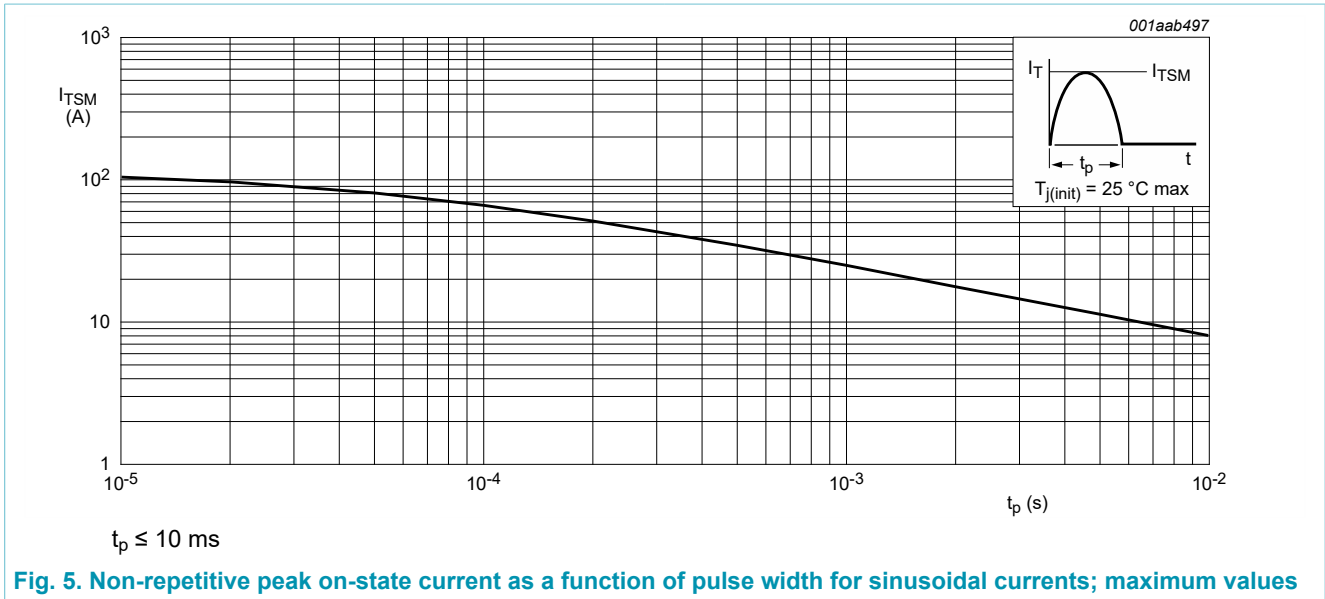


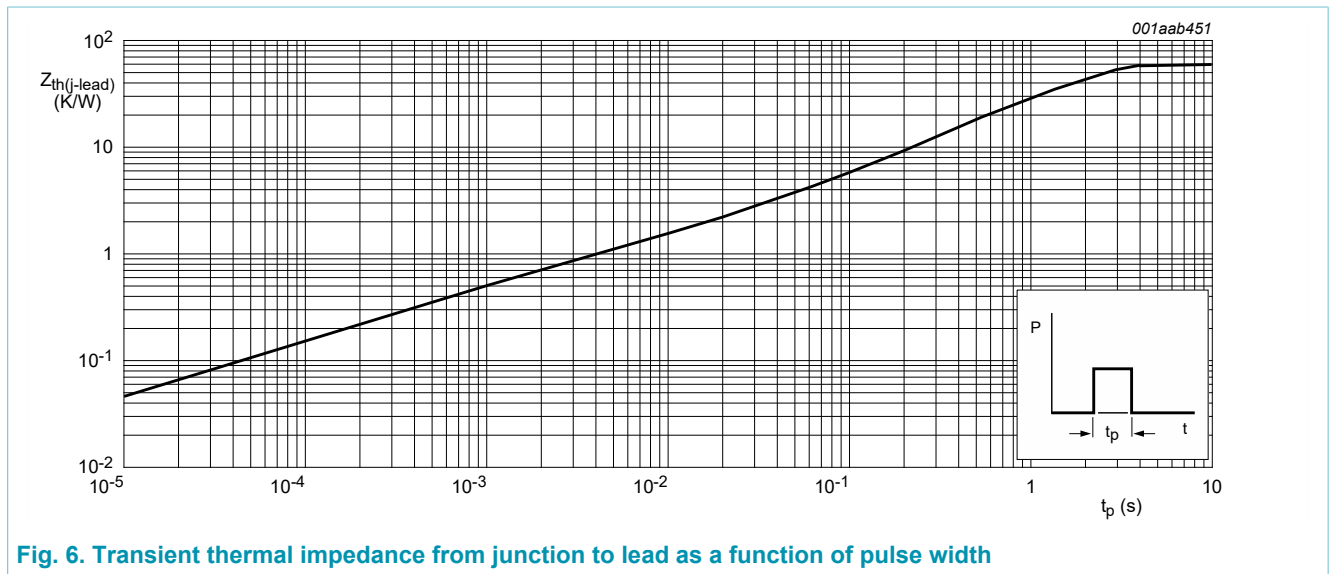
Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



8. Thermal characteristics

Table 5. Thermal characteristics

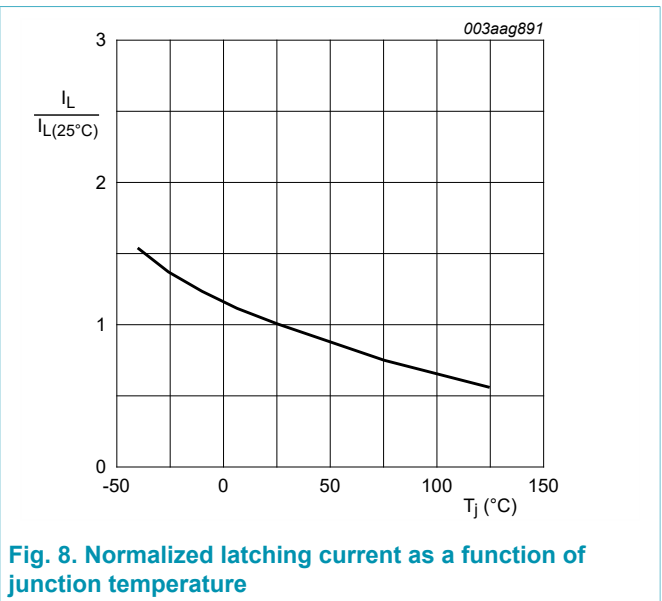
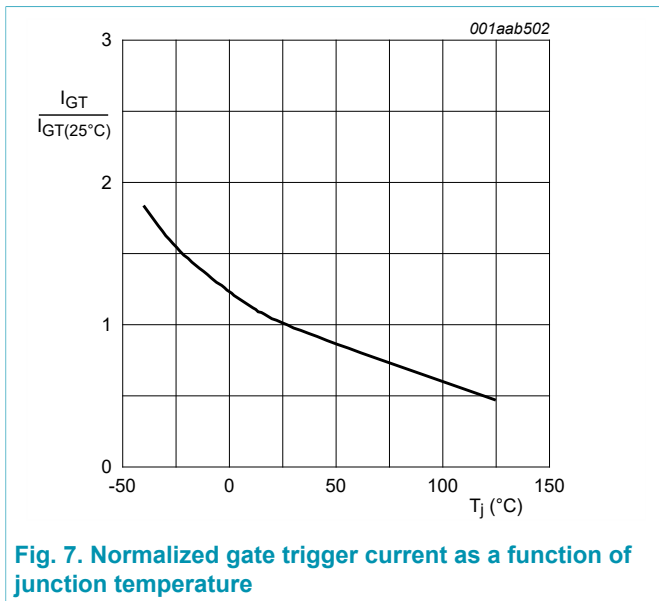
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	Fig. 6	-	-	60	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W



9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{GT}	gate trigger current	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7	-	-	50	μA
I_L	latching current	$V_D = 12\text{ V}$; $I_G = 0.5\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 8	-	2	4	mA
I_H	holding current	$V_D = 12\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 9	-	0.4	1	mA
V_T	on-state voltage	$I_T = 1.2\text{ A}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 10	-	1.25	1.7	V
V_{GT}	gate trigger voltage	$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 11	-	0.5	0.8	V
		$V_D = 12\text{ V}$; $I_T = 10\text{ mA}$; $T_j = 125\text{ }^\circ\text{C}$; Fig. 11	0.2	0.3	-	V
I_D	off-state current	$V_D = 400\text{ V}$; $R_{GK(\text{ext})} = 1\text{ k}\Omega$; $T_j = 25\text{ }^\circ\text{C}$	-	-	2	μA
		$V_D = 400\text{ V}$; $R_{GK(\text{ext})} = 1\text{ k}\Omega$; $T_j = 125\text{ }^\circ\text{C}$	-	0.05	0.1	mA
I_R	reverse current	$V_R = 400\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$; $R_{GK(\text{ext})} = 1\text{ k}\Omega$	-	0.05	2	μA
		$V_R = 400\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK(\text{ext})} = 1\text{ k}\Omega$	-	0.05	0.1	mA
Dynamic characteristics						
dV_D/dt	rate of rise of off-state voltage	$V_{DM} = 268\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; $R_{GK} = 1\text{ k}\Omega$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; Fig. 12	500	800	-	$\text{V}/\mu\text{s}$
		$V_{DM} = 268\text{ V}$; $T_j = 125\text{ }^\circ\text{C}$; ($V_{DM} = 67\%$ of V_{DRM}); exponential waveform; gate open circuit; Fig. 12	-	25	-	$\text{V}/\mu\text{s}$



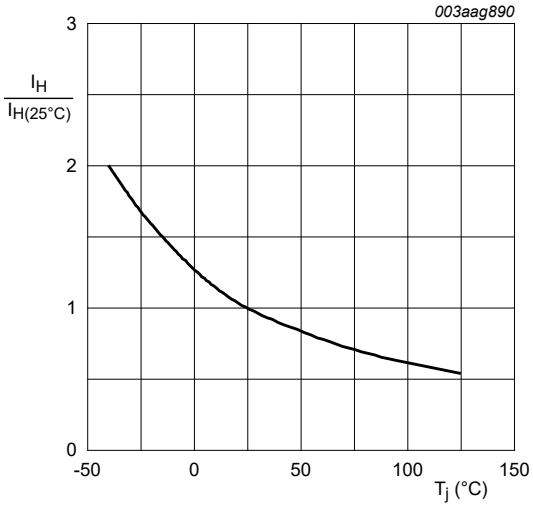
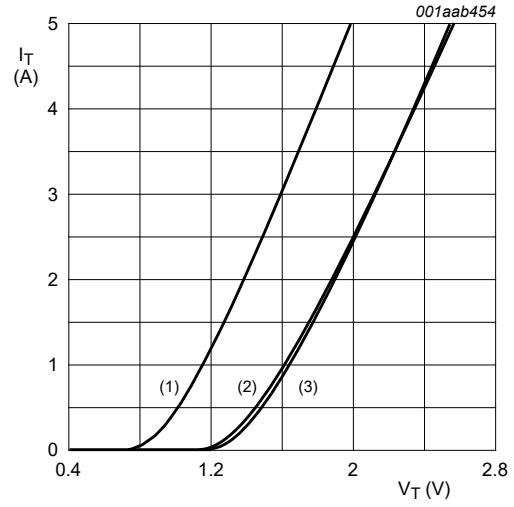


Fig. 9. Normalized holding current as a function of junction temperature



$V_o = 1.067 \text{ V}; R_s = 0.187 \Omega$

- (1) $T_j = 125 \text{ }^\circ\text{C}$; typical values
- (2) $T_j = 125 \text{ }^\circ\text{C}$; maximum values
- (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 10. On-state current as a function of on-state voltage

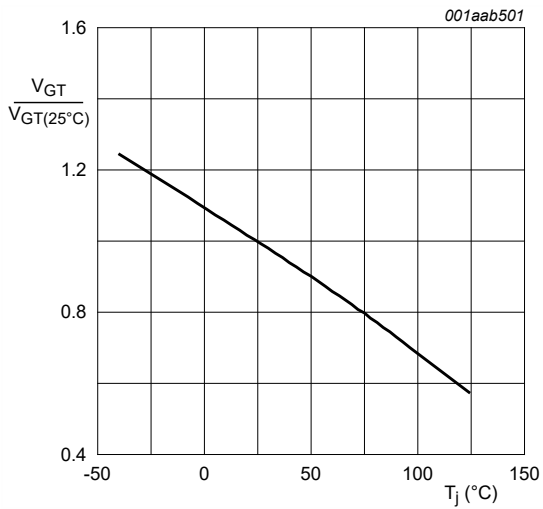
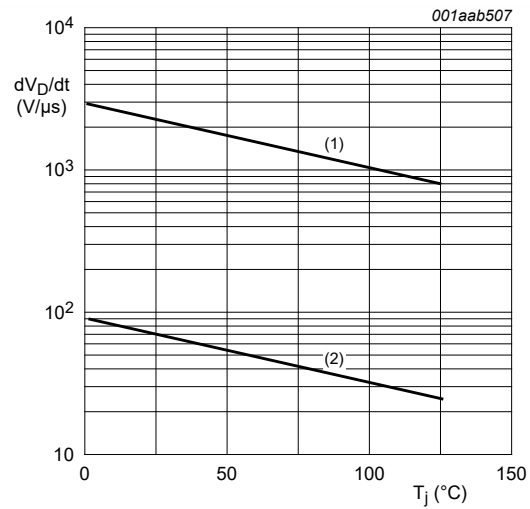


Fig. 11. Normalized gate trigger voltage as a function of junction temperature



- (1) $R_{GK} = 1 \text{ k}\Omega$
- (2) gate open circuit

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

10. Package outline



Fig. 13. Package outline TO-92 (SOT54)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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12. Contents

1. General description.....	1
2. Features and benefits.....	1
3. Applications.....	1
4. Quick reference data.....	1
5. Pinning information.....	2
6. Ordering information.....	2
7. Limiting values.....	3
8. Thermal characteristics.....	6
9. Characteristics.....	7
10. Package outline.....	9
11. Legal information.....	10

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